SEMICONDUCTOR DEVICE

ABSTRACT

There is provided a semiconductor device having excellent moisture resistance and high temperature storage properties. The semiconductor device includes a lead frame that has a die pad and an inner lead, as a substrate, a semiconductor element that is mounted on the die pad, an electrode pad that is provided in the semiconductor element, a copper wire that connects the inner lead provided on the substrate and the electrode pad, and an encapsulant resin that encapsulates the semiconductor element and the copper wire. A region of the electrode pad disposed within a range of at least equal to or less than 3 μm from a junction surface with the copper wire in a depth direction includes a metal, which is less likely to be ionized than aluminum, as a main component, and a content of sulfur in the copper wire is equal to or more than 15 ppm and equal to or less than 100 ppm with respect to a total amount of the copper wire.

[Fig.1]